



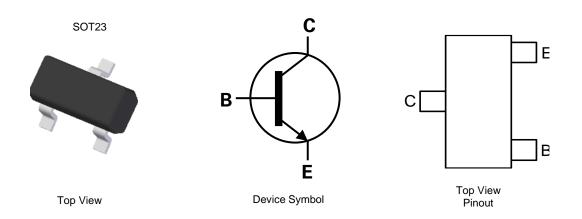
40V NPN SMALL-SIGNAL TRANSISTOR IN SOT23

Features

- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Complementary PNP Type: MMBT4403
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- An automotive-compliant part is available under separate datasheet (MMBT4401Q)

Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic "Green" Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Weight: 0.008 grams (Approximate)



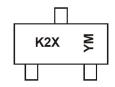
Ordering Information (Note 4)

Orderable Part Number	Package Marking Reel Size (inche		Reel Size (inches)	Tape Width (mm)	Packing	
Orderable Part Number	Package	Warking	Reel Size (Iliches)	rape widin (ililii)	Qty.	Carrier
MMBT4401-7-F	SOT23	K2X	7	8	3,000	Reel
MMBT4401-13-F	SOT23	K2X	13	8	10,000	Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



$$\begin{split} &K2X = Product\ Type\ Marking\ Code\\ &YM = Date\ Code\ Marking\\ &Y\ or\ \overline{Y}\ or\ \underline{Y} = Year\ (ex:\ M = 2025)\\ &M\ or\ \overline{M} = Month\ (ex:\ 9 = September) \end{split}$$

Date Code Key

Year	2010	-	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	Х	-	М	N	Р	R	S	Т	U	V	W	Χ
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	VCEO	40	V
Emitter-Base Voltage	VEBO	6.0	V
Collector Current	lc	600	mA
Peak Collector Current	Ісм	1	Α
Peak Base Current	Івм	200	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Dower Discipation	(Note 5)	D-	310	mW
Power Dissipation	(Note 6)	PD	350	mvv
Thermal Desistance, Junction to Ambient	(Note 5)	Devi	403	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	Reja	357	-0/00
Thermal Resistance, Junction to Leads	(Note 7)	Rejl	350	°C/W
Thermal Resistance, Junction to Case (Note 5)		Rejc	120	°C/W
Operating and Storage Temperature Range		T _J ,T _{STG}	-55 to +150	°C

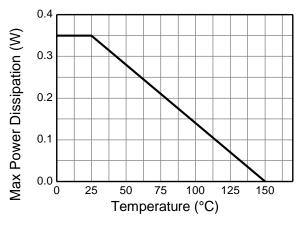
ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С
Electrostatic Discharge – Charged Device Model	ESD CDM	1,000	V	C3

- 5. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 15mm x 15mm 1oz copper.
- 8. Refer to JEDEC specification JESD22-A114, JESD22-A115 and JES-022-C101.



Thermal Characteristics and Derating Information



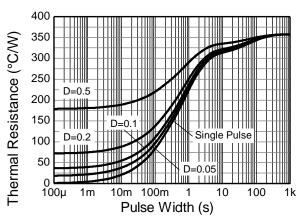
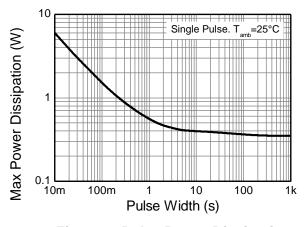


Figure 1. Derating Curve

Figure 2. Transient Thermal Impedance



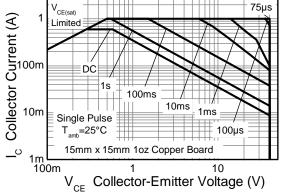


Figure 3. Pulse Power Dissipation

Figure 4. Safe Operating Area

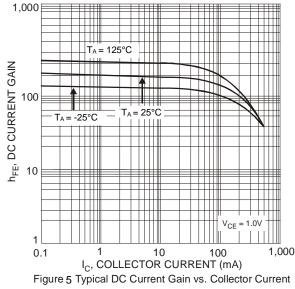


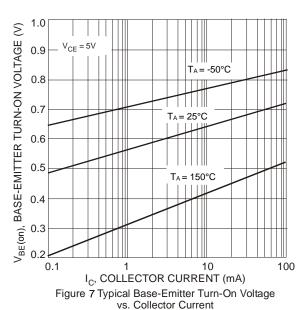
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	ВУсво	60	_	V	Ic = 100μA
Collector-Emitter Breakdown Voltage (Note 9)	BVceo	40	_	V	Ic = 10mA
Emitter-Base Breakdown Voltage	BVEBO	6	_	V	I _E = 100μA
Collector Cutoff Current	I _{CEX}		100	nA	$V_{CE} = 35V$, $V_{EB(off)} = 0.4V$
Base Cutoff Current	I _{BL}	_	100	nA	$V_{CE} = 35V$, $V_{EB(off)} = 0.4V$
ON CHARACTERISTICS (Note 9)					
DC Current Gain	hFE	20 40 80 100 40		_	Ic = 100µA, VcE = 1V Ic = 1mA, VcE = 1V Ic = 10mA, VcE = 1V Ic = 150mA, VcE = 1V Ic = 500mA, VcE = 2V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	0.4 0.75	V	$I_C = 150$ mA, $I_B = 15$ mA $I_C = 500$ mA, $I_B = 50$ mA
Base-Emitter Saturation Voltage	V _{BE} (sat)	0.75 —	0.95 1.2	V	Ic = 150mA, IB = 15mA Ic = 500mA, IB = 50mA
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance	Ccb	_	6.5	pF	$V_{CB} = 5V$, $f = 1MHz$
Input Capacitance	Ceb	_	30	pF	V _{EB} = 0.5V, f = 1MHz
Input Impedance	h _{ie}	1	15	kΩ	
Voltage Feedback Ratio	h _{re}	0.1	8	x 10 ⁻⁴	V _{CE} = 10V, I _C = 1mA,
Small-Signal Current Gain	h _{fe}	40	500	_	f = 1kHz
Output Admittance	hoe	1	30	μS	
Current Gain-Bandwidth Product	f⊤	250		MHz	V _{CE} = 10V, I _C = 20mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	td	_	15	ns	Vcc = 30V, Ic = 150mA,
Rise Time	t _r	_	20	ns	$V_{BE(off)} = 2V$, $I_{B1} = 15mA$
Storage Time	ts	_	225	ns	Vcc = 30V, Ic = 150mA,
Fall Time	t _f		30	ns	$I_{B1} = -I_{B2} = 15mA$

Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.







 $V_{CE} = 5V$ f_T, GAIN BANDWIDTH PRODUCT (MHz)

I_C, COLLECTOR CURRENT (mA) Figure 9 Typical Gain Bandwidth Product vs. Collector Current

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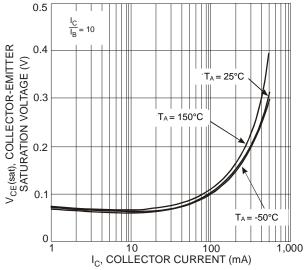


Figure 6 Collector-Emitter Saturation Voltage vs. Collector Current

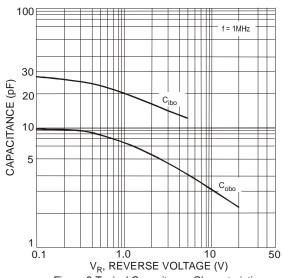


Figure 8 Typical Capacitance Characteristics

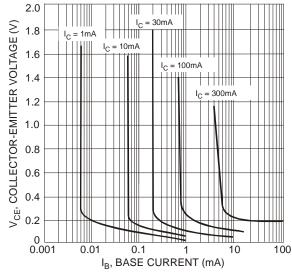


Figure 10 Typical Collector Saturation Region

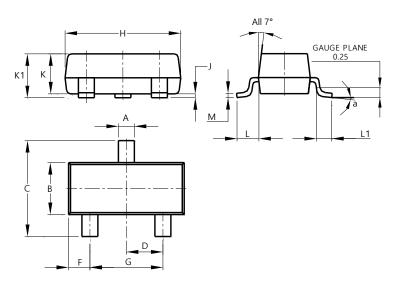
1,000



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

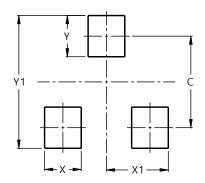


	SOT23					
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
M	0.085	0.150	0.110			
а	0°	8°				
All	Dimens	ions in	mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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